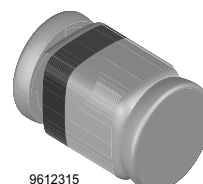


Small Signal Schottky Diode

Features

- Integrated protection ring against static discharge
- Very low forward voltage
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



9612315

Applications

- Applications where a very low forward voltage is required

Mechanical Data

Case: MicroMELF Glass case

Weight: approx. 12 mg

Cathode Band Color: Black

Packaging Codes/Options:

TR3 / 10 k per 13" reel (8 mm tape), 10 k/box

TR / 2.5 k per 7" reel (8 mm tape), 12.5 k/box

Parts Table

Part	Type differentiation	Ordering code	Remarks
BAS385	$V_R = 30\text{ V}$	BAS385-TR3 or BAS385-TR	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	30	V
Peak forward surge current	$t_p = 10\text{ ms}$	I_{FSM}	5	A
Repetitive peak forward current	$t_p \leq 1\text{ s}$	I_{FRM}	300	mA
Forward continuous current		I_F	200	mA
Average forward current	$V_{RWM} = 25\text{ V}$	I_{FAV}	200	mA

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction to ambient air	on PC board 50 mm x 50 mm x 1.6 mm	R_{thJA}	320	K/W
Junction temperature		T_j	125	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 0.1\text{ mA}$	V_F			240	mV
	$I_F = 1\text{ mA}$	V_F			320	mV
	$I_F = 10\text{ mA}$	V_F			400	mV
	$I_F = 30\text{ mA}$	V_F			500	mV
	$I_F = 100\text{ mA}$	V_F			800	mV
Reverse current	$V_R = 25\text{ V}$, $t_p = 300\text{ }\mu\text{s}$	I_R			2.3	μA
Diode capacitance	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_D			10	pF

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

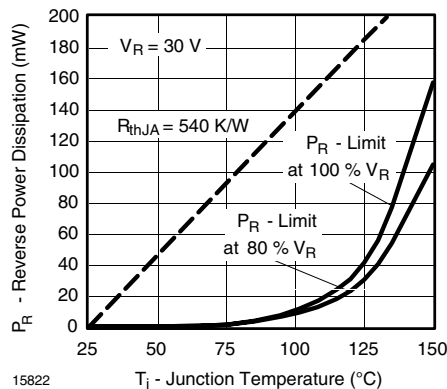


Figure 1. Max. Reverse Power Dissipation vs. Junction Temperature

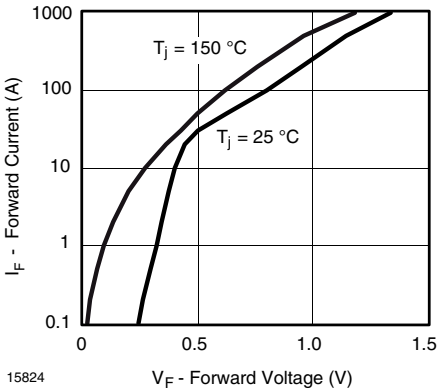


Figure 3. Forward Current vs. Forward Voltage

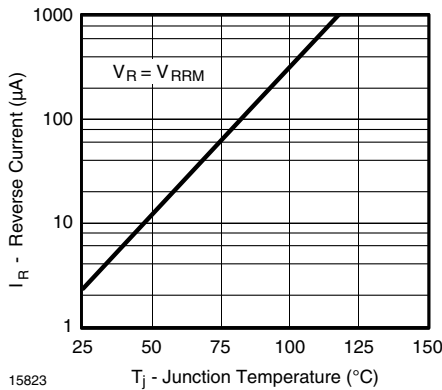


Figure 2. Reverse Current vs. Junction Temperature

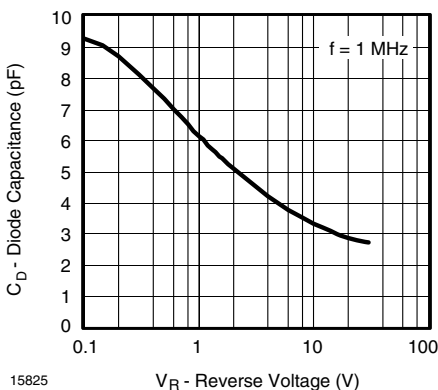


Figure 4. Diode Capacitance vs. Reverse Voltage

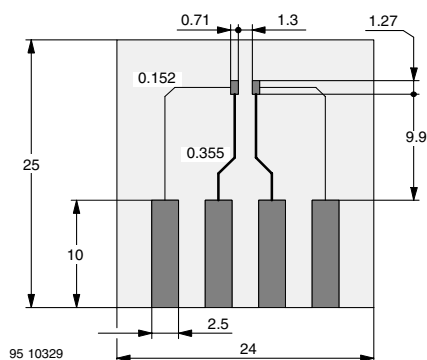
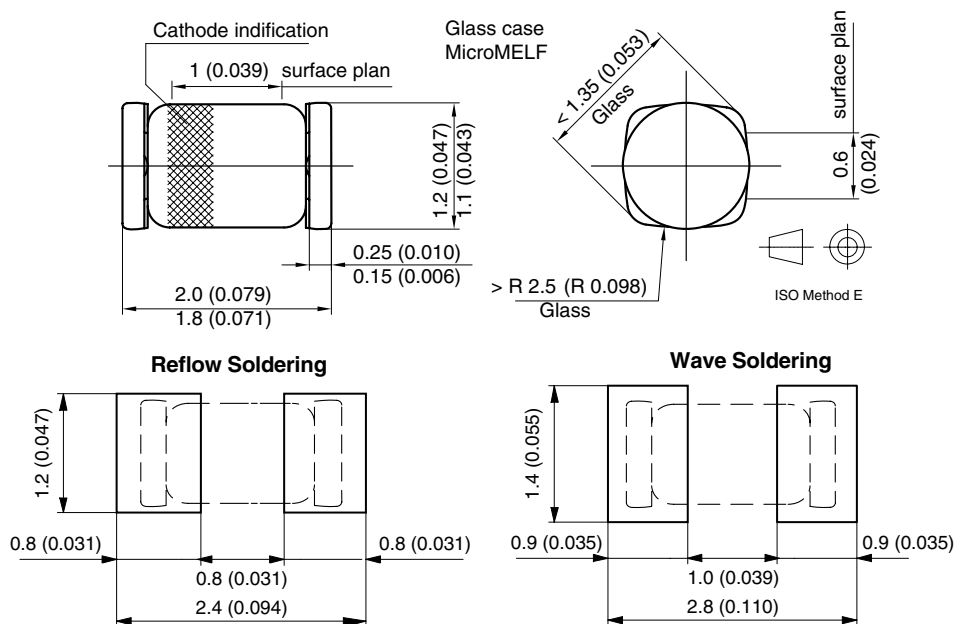


Figure 5. Board for R_{thJA} definition (in mm)

Package Dimensions in mm (Inches)



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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